## SCHOTTKY BARRIER DIODE

## Features

· Medium current schottky rectifier diode

## Applications

• For low-loss, fast-recovery, meter protection, bias isolation and clamping applications



#### Absolute Maximum Ratings (T<sub>a</sub> = 25 °C)

Parameter	Symbol	Value	Unit
Reverse Voltage	V <sub>R</sub>	40	V
Average forward current	I <sub>FAV</sub>	500	mA
Forward Current	I <sub>F</sub>	750	mA
Surge Forward Current (t ≤ 10 ms)	I <sub>FSM</sub>	2.5	А
Total Power Dissipation	P <sub>tot</sub>	600	mW
Junction Temperature	TJ	150	°C
Storage Temperature Range	T <sub>s</sub>	- 65 to + 150	°C

## Characteristics at T<sub>a</sub> = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at I <sub>F</sub> = 10 mA at I <sub>F</sub> = 250 mA	V <sub>F</sub>	0.4 0.7	V
Reverse Current at $V_R = 30 V$ at $V_R = 30 V$ , $T_a = 65 °C$	I <sub>R</sub>	50 900	μA
Diode Capacitance at $V_R$ = 10 V, f = 1 MHz	CT	12	pF







Dated : 01/09/2006

**Diode capacitance**  $C_{T} = f(V_{R})$ f = 1 MHz $T_A$  = Parameter 10 -A 40 рF 10 - ' 65°C 34 45°C 10 <sup>-6</sup> 30 5 Ř 25°0 26 10 -22 0°C 10 18 10 -8 14 **10**<sup>-10</sup> 10 6° 0 10 <sup>-11</sup> 2 4 6 8 10 12 V 15 0  $V_{\mathsf{R}}$ 

**Reverse current**  $I_{R} = f(V_{R})$ 



Forward current  $I_{F} = f(V_{F})$  $T_A$  = Parameter

Forward current  $I_{\rm F}$  =  $f(T_{\rm S})$ 











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# PACKAGE OUTLINE

## Plastic surface mounted package; 2 leads

SOD-323





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